

DATA SHEET

BSN274; BSN274A N-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

April 1995

N-channel enhancement mode vertical D-MOS transistor

BSN274; BSN274A

FEATURES

- Direct interface to C-MOS, TTL, etc., due to low threshold voltage
- High speed switching
- No secondary breakdown

DESCRIPTION

Silicon n-channel enhancement mode vertical D-MOS transistor in TO-92 variant envelope and intended for use as a line current interruptor in telephone sets and for applications in relay, high speed and line transformer drivers.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|--------------|----------------------------|------|----------|
| V_{DS} | drain-source voltage | 270 | V |
| I_D | drain current (DC) | 250 | mA |
| $R_{DS(on)}$ | drain-source on-resistance | 8 | Ω |
| $V_{GS(th)}$ | threshold voltage | 2 | V |

PINNING (BSN274)

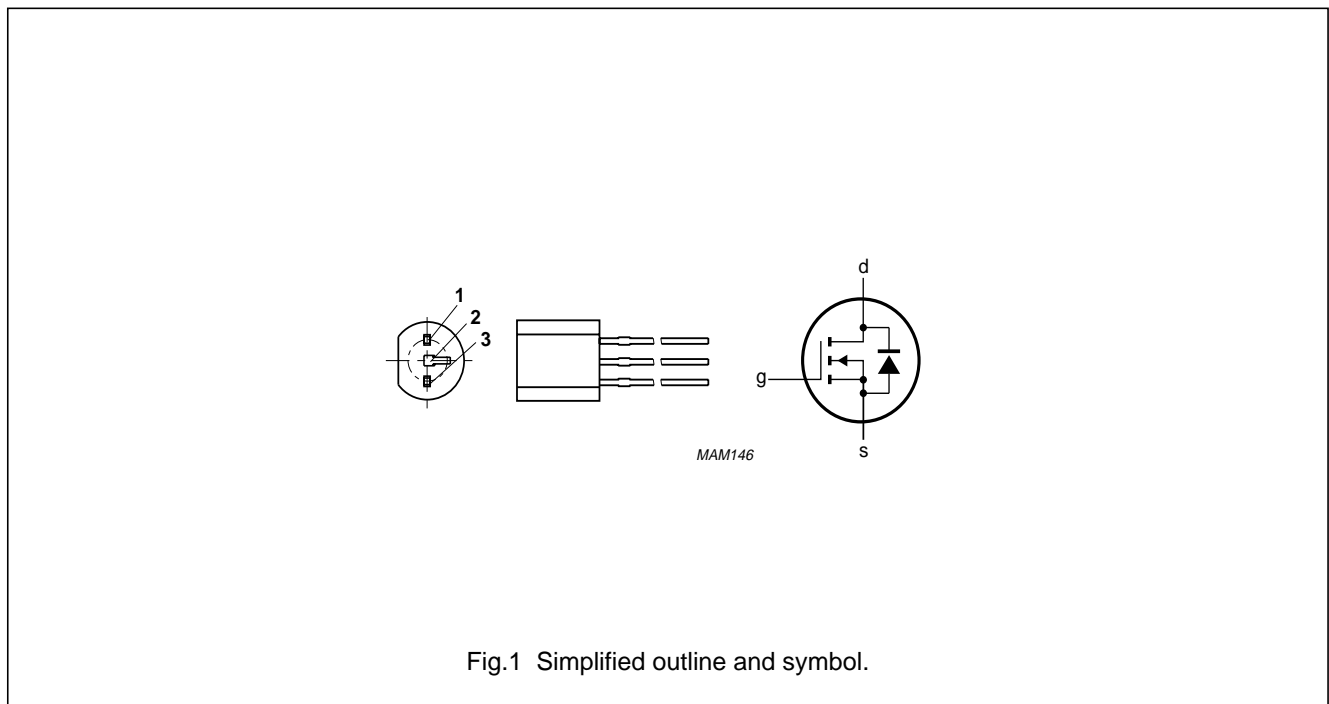
| PIN | DESCRIPTION |
|-----|-------------|
| 1 | gate |
| 2 | drain |
| 3 | source |

PINNING (BSN274A)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | source |
| 2 | gate |
| 3 | drain |

Note: Other pinnings are available on request.

PIN CONFIGURATION - TO-92 VARIANT



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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|---------------|--------------------------------|---|------|------|------|
| V_{DS} | drain-source voltage | | – | 270 | V |
| $\pm V_{GSO}$ | gate-source voltage | open drain | – | 20 | V |
| I_D | drain current | DC | – | 250 | mA |
| I_{DM} | drain current | peak | – | 1 | A |
| P_{tot} | total power dissipation | up to $T_{amb} = 25\text{ °C}$ (note 1) | – | 1 | W |
| T_{stg} | storage temperature range | | –65 | 150 | °C |
| T_j | operating junction temperature | | – | 150 | °C |

THERMAL RESISTANCE

| SYMBOL | PARAMETER | VALUE | UNIT |
|---------------|-----------------------------------|-------|------|
| $R_{th\ j-a}$ | from junction to ambient (note 1) | 125 | K/W |

Notes

1. Transistor mounted on printed circuit board, maximum lead length 4 mm, mounting pad for drain leads minimum 10 mm × 10 mm.

CHARACTERISTICS

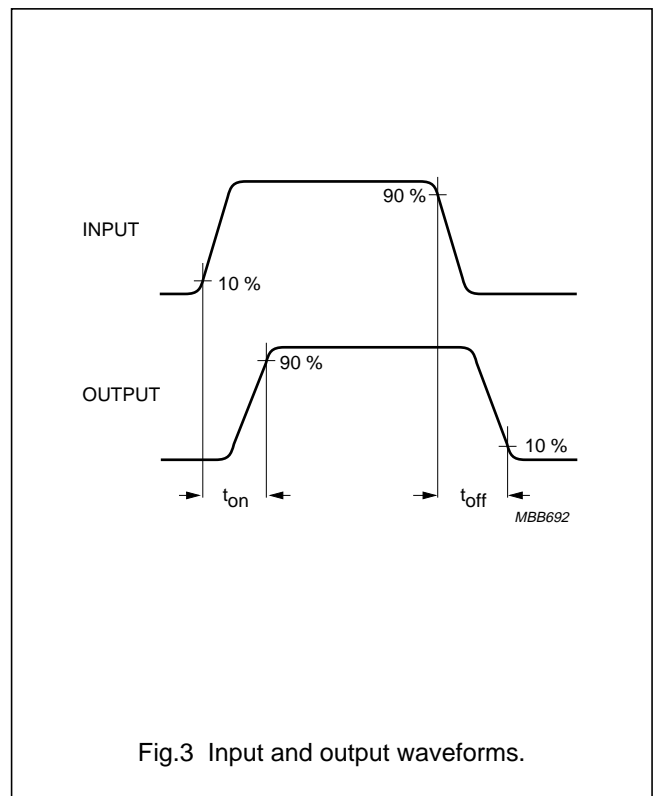
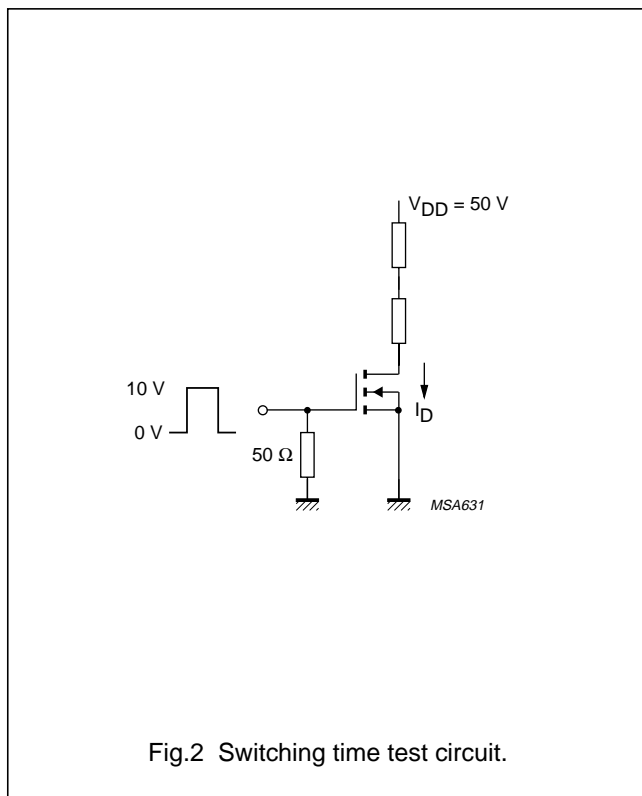
 $T_j = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|--------------------------------|--|------|------|------|---------------|
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $V_{GS} = 0$ $I_D = 10\ \mu\text{A}$ | 270 | – | – | V |
| I_{DSS} | drain-source leakage current | $V_{DS} = 220\text{ V}$ $V_{GS} = 0$ | – | – | 1 | μA |
| $\pm I_{GSS}$ | gate-source leakage current | $\pm V_{GS} = 20\text{ V}$ $V_{DS} = 0$ | – | – | 100 | nA |
| $V_{GS(th)}$ | gate threshold voltage | $I_D = 1\text{ mA}$ $V_{DS} = V_{GS}$ | 0.8 | – | 2 | V |
| $R_{DS(on)}$ | drain-source on-resistance | $I_D = 250\text{ mA}$ $V_{GS} = 10\text{ V}$ | – | 6.5 | 8 | Ω |
| $R_{DS(on)}$ | drain-source on-resistance | $I_D = 20\text{ mA}$ $V_{GS} = 2.4\text{ V}$ | – | 9 | 14 | Ω |
| $ Y_{fs} $ | transfer admittance | $I_D = 250\text{ mA}$ $V_{DS} = 25\text{ V}$ | 200 | 400 | – | mS |
| C_{iss} | input capacitance | $V_{DS} = 25\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$ | – | 65 | 90 | pF |
| C_{oss} | output capacitance | $V_{DS} = 25\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$ | – | 20 | 30 | pF |

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| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|----------------------|---|------|------|------|------|
| C_{rss} | feedback capacitance | $V_{DS} = 25\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$ | – | 5 | 15 | pF |
| Switching times (see Figs 2 and 3) | | | | | | |
| t_{on} | switching-on time | $I_D = 250\text{ mA}$ $V_{DD} = 50\text{ V}$ $V_{GS} = 0\text{ to }10\text{ V}$ | – | 5 | 10 | ns |
| t_{off} | switching-off time | $I_D = 250\text{ mA}$ $V_{DD} = 50\text{ V}$ $V_{GS} = 0\text{ to }10\text{ V}$ | – | 20 | 30 | ns |



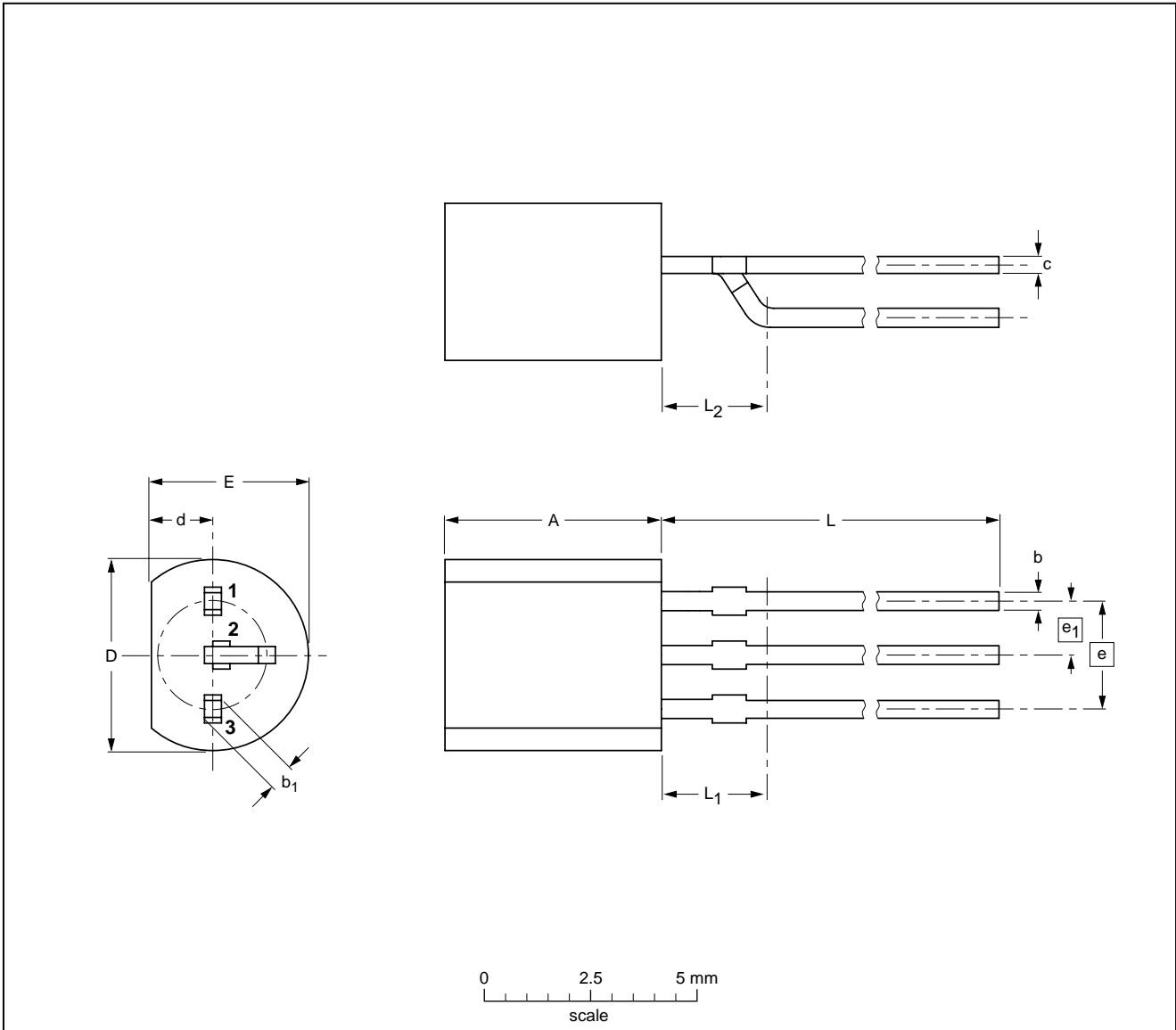
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PACKAGE OUTLINES

Plastic single-ended leaded (through hole) package; 3 leads (on-circle)

SOT54 variant



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b | b_1 | c | D | d | E | e | e_1 | L | $L_1^{(1)}$ max | L_2 max |
|------|------------|--------------|--------------|--------------|------------|------------|------------|------|-------|--------------|--------------------|--------------|
| mm | 5.2 5.0 | 0.48 0.40 | 0.66 0.56 | 0.45 0.40 | 4.8 4.4 | 1.7 1.4 | 4.2 3.6 | 2.54 | 1.27 | 14.5 12.7 | 2.5 | 2.5 |

Notes

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|-------|------------------------|------------|
| | IEC | JEDEC | EIAJ | | |
| SOT54 variant | | TO-92 | SC-43 | | 97-04-14 |

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DEFINITIONS

| Data sheet status | |
|---|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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